



DTB123ECT116 Information



For Reference Only

Part Number DTB123ECT116

Manufacturer Rohm Semiconductor

Category Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Single, Pre-Biased

Description PNP -500MA/-50V DIGITAL TRANSIST

Package TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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DTB123ECT116 Specifications

Manufacturer Part NumberDTB123ECT116ManufacturerRohm SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - Single, Pre-BiasedPackageTO-236-3, SC-59, SOT-23-3Series-Transistor TypePNP - Pre-BiasedCurrent - Collector (Ic) (Max)500mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)2.2kResistor - Emitter Base (R2) (Ohms)2.2kDC Current Gain (hFE) (Min) @ Ic, Vce39 @ 50mA, 5VVce Saturation (Max) @ Ib, Ic300mV @ 2.5mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition200MHzPower - Max200mW
Category Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single, Pre-Biased Package TO-236-3, SC-59, SOT-23-3 Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic 300mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single, Pre-Biased - TO-236-3, SC-59, SOT-23-3 Series - 300mA 500mA 500mA 500mA 500mA 500mA
Transistors - Bipolar (BJT) - Single, Pre-Biased TO-236-3, SC-59, SOT-23-3 Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition Transistors - Bipolar (BJT) - Single, Pre-Biased TO-236-3, SC-59, SOT-23-3 - 200MHz
Package TO-236-3, SC-59, SOT-23-3 Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition TO-236-3, SC-59, SOT-23-3 - 300mA 500mA 500mA 500mA 500mA 500mA 500mA
Series - Transistor Type PNP - Pre-Biased Current - Collector (Ic) (Max) 500mA Voltage - Collector Emitter Breakdown (Max) 50V Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) 2.2k DC Current Gain (hFE) (Min) @ Ic, Vce 39 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 300mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) 500nA Frequency - Transition 200MHz
Transistor Type Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition PNP - Pre-Biased 500mA 500mA 50V 2.2k 2.2k 30mV @ 2.5mA, 50mA 500nA 500nA
Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 39 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition 500mA 500mA 500mA 500mA
Voltage - Collector Emitter Breakdown (Max) Resistor - Base (R1) (Ohms) 2.2k Resistor - Emitter Base (R2) (Ohms) 2.2k DC Current Gain (hFE) (Min) @ Ic, Vce 39 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 300mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 200MHz
Resistor - Base (R1) (Ohms) Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 39 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition 2.2k 39 @ 50mA, 5V 300mV @ 2.5mA, 50mA 500nA
Resistor - Emitter Base (R2) (Ohms) DC Current Gain (hFE) (Min) @ Ic, Vce 39 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) Frequency - Transition 200MHz
DC Current Gain (hFE) (Min) @ Ic, Vce 39 @ 50mA, 5V Vce Saturation (Max) @ Ib, Ic 300mV @ 2.5mA, 50mA Current - Collector Cutoff (Max) Frequency - Transition 200MHz
Vce Saturation (Max) @ Ib, Ic300mV @ 2.5mA, 50mACurrent - Collector Cutoff (Max)500nAFrequency - Transition200MHz
Current - Collector Cutoff (Max) 500nA Frequency - Transition 200MHz
Frequency - Transition 200MHz
Power - Max 200mW
Mounting Type Surface Mount
Package / Case TO-236-3, SC-59, SOT-23-3
Supplier Device Package SST3
Report errors?

DTB123ECT116 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

DTB123ECT116 Payment Methods





















DTB123ECT116 Shipping Methods













If you have any question about DTB123ECT116, please do not hesitate to contact us!

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